

TECHNICAL DAT  
DATA SHEET 1008, REV. -

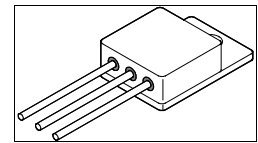
## HERMETIC POWER SCHOTTKY RECTIFIER Low Forward Voltage Drop (60 V, 35A)

**Applications:**

- Switching Power Supply • Converters • Free-Wheeling Diodes • Polarity Protection Diode

**Features:**

- Soft Reverse Recovery at Low and High Temperature
- Low Forward Voltage Drop
- Low Reverse Leakage Current
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics



**Maximum Ratings:**

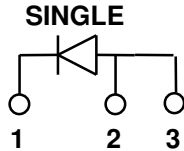
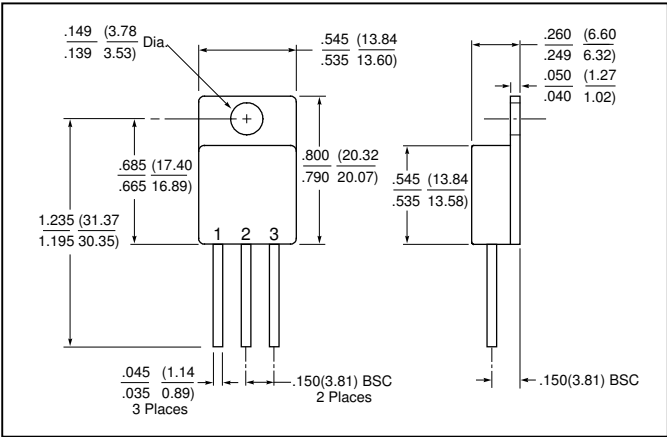
Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	$V_{RWM}$	-	60	V
Max. Average Forward Current	$I_{F(AV)}$	50% duty cycle @ $T_C = 100^\circ\text{C}$ , rectangular wave form	35	A
Max. Peak One Cycle Non-Repetitive Surge Current	$I_{FSM}$	8.3 ms, half Sine pulse	150	A
Max. Junction Temperature	$T_J$	-	-65 to +150	$^\circ\text{C}$
Max. Storage Temperature	$T_{stg}$	-	-65 to +150	$^\circ\text{C}$

**Electrical Characteristics:**

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	$V_{F1}$	@ 35 A, Pulse, $T_J = 25^\circ\text{C}$	0.65	V
	$V_{F2}$	@ 35 A, Pulse, $T_J = 125^\circ\text{C}$	0.54	V
Max. Reverse Current	$I_{R1}$	@ $V_R = 60\text{V}$ , Pulse, $T_J = 25^\circ\text{C}$	9.0	mA
	$I_{R2}$	@ $V_R = 60\text{V}$ , Pulse, $T_J = 125^\circ\text{C}$	420	mA
Max. Junction Capacitance	$C_T$	@ $V_R = 5\text{V}$ , $T_C = 25^\circ\text{C}$ $f_{SIG} = 1\text{MHz}$ , $V_{SIG} = 50\text{mV (p-p)}$	4800	pF
Maximum Thermal Resis.	$R_{\theta JC}$	-	0.33	$^\circ\text{C/W}$

**TECHNICAL DATA**  
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**Mechanical Dimensions: In Inches / mm**



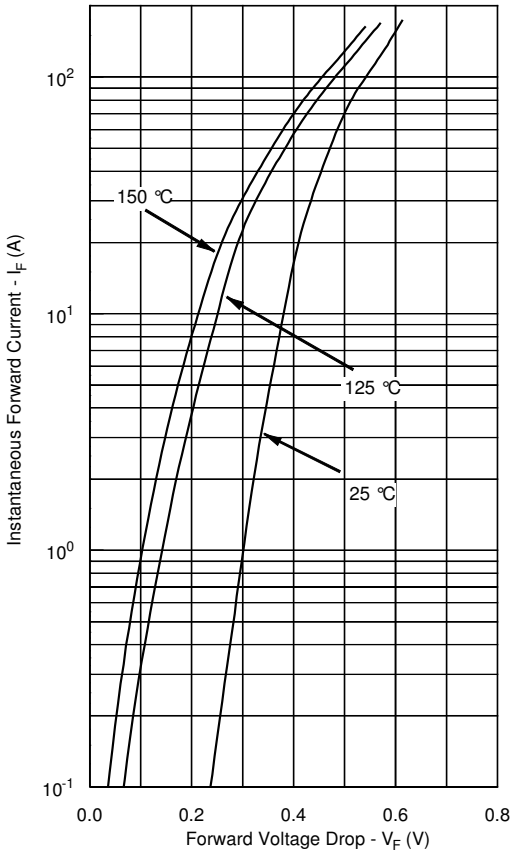
**TO-254**

**PINOUT TABLE**

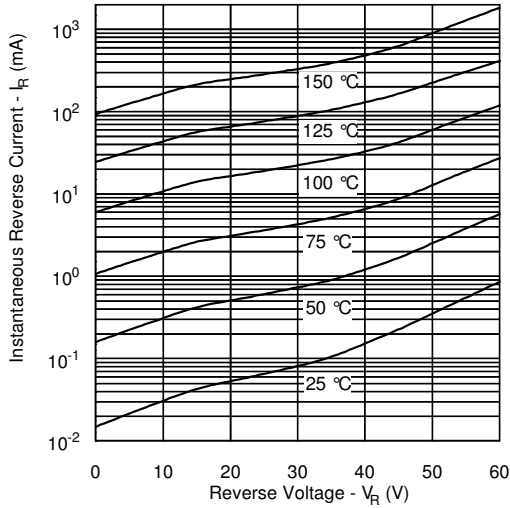
TYPE	PIN 1	PIN 2	PIN 3
SINGLE RECTIFIER	CATHODE	ANODE	ANODE

**Note:** The  $V_f$  curves shown are for the un-packaged die only.

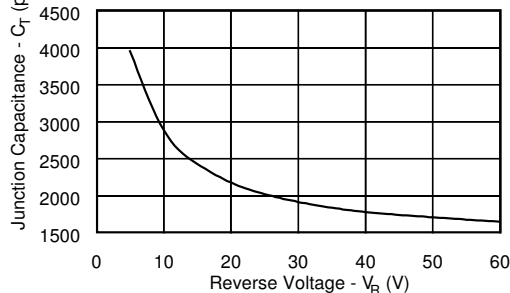
**Typical Forward Characteristics**



**Typical Reverse Characteristics**



**Typical Junction Capacitance**



**TECHNICAL DATA**

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